The S-8203A Series includes high-accuracy voltage detection circuits and delay circuits, in single use, makes it possible for users to monitor the status of 3-series cell lithium-ion rechargeable battery. The S-8203A Series is suitable for protecting lithium-ion rechargeable battery pack from overcharge, overdischarge, and overcurrent.

**Features**

- High-accuracy voltage detection function for each cell
  - Overcharge detection voltage n (n = 1 to 3) 3.55 V to 4.50 V\(^n\) (50 mV step) Accuracy ±25 mV
  - Overcharge release voltage n (n = 1 to 3) 3.30 V to 4.50 V\(^n\) Accuracy ±50 mV
  - Overdischarge detection voltage n (n = 1 to 3) 2.0 V to 3.2 V\(^n\) (100 mV step) Accuracy ±80 mV
  - Overdischarge release voltage n (n = 1 to 3) 2.0 V to 3.4 V\(^n\) Accuracy ±100 mV
- Discharge overcurrent detection in 2-step
  - Discharge overcurrent detection voltage 0.05 V to 0.30 V\(^n\) (50 mV step) Accuracy ±15 mV
  - Short-circuiting detection voltage 0.50 V to 1.0 V\(^n\) (100 mV step) Accuracy ±100 mV
- Charge overcurrent detection function
  - Charge overcurrent detection voltage −0.30 V to −0.05 V (50 mV step) Accuracy ±30 mV
- Settable by external capacitor; overcharge detection delay time, overdischarge detection delay time, discharge overcurrent detection delay time, charge overcurrent detection delay time
  (Load short-circuiting detection delay time is internally fixed.)
- Independent charge and discharge control by the control pins
- Power-down function is selectable: Available, unavailable
- High-withstand voltage: Absolute maximum rating 28 V
- Wide operation voltage range: 2 V to 24 V
- Wide operation temperature range: Ta = −40°C to +85°C
- Low current consumption
  - During operation: 40 μA max. (Ta = +25°C)
  - During power-down: 0.1 μA max. (Ta = +25°C)
- Lead-free (Sn 100%), halogen-free

*1. The overcharge detection voltage n (n = 1 to 3) and overdischarge detection voltage (n = 1 to 3) cannot be selected if the voltage difference between them is 0.6 V or lower.

*2. Overcharge hysteresis voltage n (n = 1 to 3) can be selected as 0 V or from a range of 0.1 V to 0.4 V in 50 mV step.

*3. Overdischarge hysteresis voltage n (n = 1 to 3) can be selected as 0 V or from a range of 0.2 V to 0.7 V in 100 mV step.

*4. The discharge overcurrent detection voltage and load short-circuiting detection voltage cannot be selected if the voltage difference between them is 0.3 V or lower.

**Application**

- Rechargeable lithium-ion battery pack

**Package**

- 16-Pin TSSOP
**Block Diagram**

Remark  Diodes in the figure are parasitic diodes.

Figure 1
■ Product Name Structure

1. Product name

S-8203A xx - TCT1 U

- Environmental code
  U: Lead-free (Sn 100%), halogen-free

- Package abbreviation and IC packing specifications
  TCT1: 16-Pin TSSOP, Tape

- Serial code
  Sequentially set from AA to ZZ

*1. Refer to the tape drawing.
*2. Refer to "3. Product name list".

2. Package

<table>
<thead>
<tr>
<th>Package Name</th>
<th>Dimension</th>
<th>Tape</th>
<th>Reel</th>
</tr>
</thead>
</table>
3. Product name list

Table 2

<table>
<thead>
<tr>
<th></th>
<th></th>
<th></th>
<th></th>
<th></th>
<th></th>
<th></th>
<th></th>
<th></th>
<th></th>
<th></th>
</tr>
</thead>
<tbody>
<tr>
<td>S-8203AAA-TCT1U</td>
<td>4.250 V</td>
<td>4.150 V</td>
<td>2.70 V</td>
<td>3.00 V</td>
<td>0.20 V</td>
<td>0.50 V</td>
<td>-0.10 V</td>
<td>Available</td>
<td>Available</td>
<td>(2)</td>
</tr>
<tr>
<td>S-8203AAB-TCT1U</td>
<td>4.250 V</td>
<td>4.150 V</td>
<td>2.50 V</td>
<td>3.00 V</td>
<td>0.10 V</td>
<td>0.50 V</td>
<td>-0.05 V</td>
<td>Available</td>
<td>Available</td>
<td>(2)</td>
</tr>
<tr>
<td>S-8203AAC-TCT1U</td>
<td>4.250 V</td>
<td>4.150 V</td>
<td>2.50 V</td>
<td>3.00 V</td>
<td>0.10 V</td>
<td>0.50 V</td>
<td>-0.05 V</td>
<td>Available</td>
<td>Unavailable</td>
<td>(2)</td>
</tr>
<tr>
<td>S-8203AAD-TCT1U</td>
<td>4.250 V</td>
<td>4.100 V</td>
<td>3.00 V</td>
<td>3.20 V</td>
<td>0.15 V</td>
<td>0.50 V</td>
<td>-0.10 V</td>
<td>Available</td>
<td>Available</td>
<td>(2)</td>
</tr>
<tr>
<td>S-8203AEE-TCT1U</td>
<td>4.350 V</td>
<td>4.150 V</td>
<td>2.40 V</td>
<td>3.00 V</td>
<td>0.15 V</td>
<td>0.50 V</td>
<td>-0.10 V</td>
<td>Available</td>
<td>Available</td>
<td>(2)</td>
</tr>
<tr>
<td>S-8203AAG-TCT1U</td>
<td>4.350 V</td>
<td>4.150 V</td>
<td>2.80 V</td>
<td>3.00 V</td>
<td>0.20 V</td>
<td>0.50 V</td>
<td>-0.10 V</td>
<td>Available</td>
<td>Available</td>
<td>(2)</td>
</tr>
<tr>
<td>S-8203AHH-TCT1U</td>
<td>3.660 V</td>
<td>3.500 V</td>
<td>2.20 V</td>
<td>2.30 V</td>
<td>0.10 V</td>
<td>0.50 V</td>
<td>-0.05 V</td>
<td>Available</td>
<td>Available</td>
<td>(2)</td>
</tr>
<tr>
<td>S-8203AII-TCT1U</td>
<td>3.750 V</td>
<td>3.600 V</td>
<td>2.00 V</td>
<td>2.50 V</td>
<td>0.15 V</td>
<td>0.50 V</td>
<td>-0.10 V</td>
<td>Available</td>
<td>Available</td>
<td>(2)</td>
</tr>
</tbody>
</table>

*1. The delay time is set by the external capacitor.

But the discharge overcurrent release delay time (t_DIOVR) and charge overcurrent release delay time (t_CIOVR) are calculated by discharge overcurrent detection delay time (t_DIOV) and charge overcurrent detection delay time (t_CIOV) as the following equations. 1 [ms] (typ.) is the internal delay time of the S-8203A Series.

(1) \[ t_{DIOVR} = t_{DIOV} \times 10 + 1 \] [ms] (typ.), \[ t_{CIOVR} = t_{CIOV} \times 10 + 1 \] [ms] (typ.)
(2) \[ t_{DIOVR} = t_{DIOV} \times 0.05 + 1 \] [ms] (typ.), \[ t_{CIOVR} = t_{CIOV} \times 0.05 + 1 \] [ms] (typ.)

Moreover, refer to “7. Delay time setting” in “Operation” for calculational methods of delay times.

Remark Please contact our sales office for products with detection voltage values other than those specified above.
Pin Configuration

Figure 2

<table>
<thead>
<tr>
<th>Pin No.</th>
<th>Symbol</th>
<th>Description</th>
</tr>
</thead>
<tbody>
<tr>
<td>1</td>
<td>VM</td>
<td>Voltage detection pin between VSS pin and VM pin</td>
</tr>
<tr>
<td>2</td>
<td>CO</td>
<td>FET gate connection pin for charge control (Pch open-drain output) Pin for voltage detection between VSS pin and CO pin</td>
</tr>
<tr>
<td>3</td>
<td>DO</td>
<td>FET gate connection pin for discharge control (CMOS output) Pin for voltage detection between VSS pin and VINI pin</td>
</tr>
<tr>
<td>4</td>
<td>VINI</td>
<td>Control pin for charge FET</td>
</tr>
<tr>
<td>5</td>
<td>CTLC</td>
<td>Control pin for discharge FET</td>
</tr>
<tr>
<td>6</td>
<td>CTLD</td>
<td>Control pin for discharge FET</td>
</tr>
<tr>
<td>7</td>
<td>CCT</td>
<td>Capacitor connection pin for delay for overcharge detection voltage</td>
</tr>
<tr>
<td>8</td>
<td>CDT</td>
<td>Capacitor connection pin for delay for overdischarge detection voltage</td>
</tr>
<tr>
<td>9</td>
<td>CIT</td>
<td>Capacitor connection pin for delay for discharge overcurrent detection, charge overcurrent detection</td>
</tr>
<tr>
<td>10</td>
<td>VSS</td>
<td>Input pin for negative power supply *1</td>
</tr>
<tr>
<td>11</td>
<td>NPI</td>
<td>Input pin for negative power supply *1</td>
</tr>
<tr>
<td>12</td>
<td>VC4</td>
<td>Connection pin for battery 3's negative voltage Input pin for negative power supply</td>
</tr>
<tr>
<td>13</td>
<td>VC3</td>
<td>Connection pin for battery 2's negative voltage Connection pin for battery 3's positive voltage</td>
</tr>
<tr>
<td>14</td>
<td>VC2</td>
<td>Connection pin for battery 1's negative voltage Connection pin for battery 2's positive voltage</td>
</tr>
<tr>
<td>15</td>
<td>VC1</td>
<td>Connection pin for battery 1's positive voltage</td>
</tr>
<tr>
<td>16</td>
<td>VDD</td>
<td>Input pin for positive power supply Connection pin for battery 1's positive voltage</td>
</tr>
</tbody>
</table>

*1. Be sure to short the VSS pin and the NPI pin when using them.
Absolute Maximum Ratings

Table 4

<table>
<thead>
<tr>
<th>Item</th>
<th>Symbol</th>
<th>Applied Pin</th>
<th>Absolute Maximum Rating</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>Input voltage between VDD pin and VSS pin</td>
<td>V_DS</td>
<td>VDD</td>
<td>V_DD - 0.3 to V_SS + 28</td>
<td>V</td>
</tr>
<tr>
<td>Input pin voltage 1</td>
<td>V_IN1</td>
<td>VC1, VC2, VC3, VC4, NPI, CTLC, CTLD, CCT, CDT, CIT</td>
<td>V_DD - 0.3 to V_DD + 0.3</td>
<td>V</td>
</tr>
<tr>
<td>Input pin voltage 2</td>
<td>V_IN2</td>
<td>VM, VINI</td>
<td>V_DD - 28 to V_DD + 0.3</td>
<td>V</td>
</tr>
<tr>
<td>DO pin output voltage</td>
<td>V_DO</td>
<td>DO</td>
<td>V_SS - 0.3 to V_DD + 0.3</td>
<td>V</td>
</tr>
<tr>
<td>CO pin input and output voltage</td>
<td>V_CO</td>
<td>CO</td>
<td>V_DD - 28 to V_DD + 0.3</td>
<td>V</td>
</tr>
<tr>
<td>Power dissipation</td>
<td>P_D</td>
<td>–</td>
<td>1100*1 mW</td>
<td></td>
</tr>
<tr>
<td>Operation ambient temperature</td>
<td>T_op</td>
<td>–</td>
<td>-40 to +85°C</td>
<td></td>
</tr>
<tr>
<td>Storage temperature</td>
<td>T_stg</td>
<td>–</td>
<td>-40 to +125°C</td>
<td></td>
</tr>
</tbody>
</table>

*1. When mounted on board

[Mounted board]

(1) Board size: 114.3 mm × 76.2 mm × t1.6 mm

(2) Board name: JEDEC STANDARD51-7

Caution: The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

Figure 3: Power Dissipation of Package (When Mounted on Board)
### Electrical Characteristics

#### Table 5 (1 / 2)

(Ta = +25°C unless otherwise specified)

<table>
<thead>
<tr>
<th>Item</th>
<th>Symbol</th>
<th>Condition</th>
<th>Min.</th>
<th>Typ.</th>
<th>Max.</th>
<th>Unit</th>
<th>Test Circuit</th>
</tr>
</thead>
<tbody>
<tr>
<td><strong>Detection Voltage</strong></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Overcharge detection voltage n (n = 1, 2, 3)</td>
<td>( V_{\text{CU}} )</td>
<td>( V_1 = V_2 = V_3 = V_{\text{CU}} - 0.05 ) V</td>
<td>( V_{\text{CU}} - 0.025 )</td>
<td>( V_{\text{CU}} )</td>
<td>( V_{\text{CU}} + 0.025 )</td>
<td>V</td>
<td>2</td>
</tr>
<tr>
<td>Overcharge release voltage n (n = 1, 2, 3)</td>
<td>( V_{\text{CL}} )</td>
<td>–</td>
<td>( V_{\text{CL}} - 0.05 )</td>
<td>( V_{\text{CL}} )</td>
<td>( V_{\text{CL}} + 0.05 )</td>
<td>V</td>
<td>2</td>
</tr>
<tr>
<td>Overdischarge detection voltage n (n = 1, 2, 3)</td>
<td>( V_{\text{DL}} )</td>
<td>–</td>
<td>( V_{\text{DL}} - 0.08 )</td>
<td>( V_{\text{DL}} )</td>
<td>( V_{\text{DL}} + 0.08 )</td>
<td>V</td>
<td>2</td>
</tr>
<tr>
<td>Overdischarge release voltage n (n = 1, 2, 3)</td>
<td>( V_{\text{DU}} )</td>
<td>–</td>
<td>( V_{\text{DU}} - 0.10 )</td>
<td>( V_{\text{DU}} )</td>
<td>( V_{\text{DU}} + 0.10 )</td>
<td>V</td>
<td>2</td>
</tr>
<tr>
<td>Discharge overcurrent detection voltage</td>
<td>( V_{\text{DIOV}} )</td>
<td>–</td>
<td>( V_{\text{DIOV}} - 0.015 )</td>
<td>( V_{\text{DIOV}} )</td>
<td>( V_{\text{DIOV}} + 0.015 )</td>
<td>V</td>
<td>2</td>
</tr>
<tr>
<td>Load short-circuiting detection voltage</td>
<td>( V_{\text{SHORT}} )</td>
<td>–</td>
<td>( V_{\text{SHORT}} - 0.10 )</td>
<td>( V_{\text{SHORT}} )</td>
<td>( V_{\text{SHORT}} + 0.10 )</td>
<td>V</td>
<td>2</td>
</tr>
<tr>
<td>Charge overcurrent detection voltage</td>
<td>( V_{\text{CIOV}} )</td>
<td>–</td>
<td>( V_{\text{CIOV}} - 0.03 )</td>
<td>( V_{\text{CIOV}} )</td>
<td>( V_{\text{CIOV}} + 0.03 )</td>
<td>V</td>
<td>2</td>
</tr>
<tr>
<td>Temperature coefficient 1 (^{1})</td>
<td>( T_{\text{COE1}} )</td>
<td>( Ta = 0°C ) to ( +50°C )</td>
<td>–1.0</td>
<td>0</td>
<td>0.9</td>
<td>mV/°C</td>
<td>–</td>
</tr>
<tr>
<td>Temperature coefficient 2 (^{2})</td>
<td>( T_{\text{COE2}} )</td>
<td>( Ta = 0°C ) to ( +50°C )</td>
<td>–0.5</td>
<td>0</td>
<td>0.5</td>
<td>mV/°C</td>
<td>–</td>
</tr>
<tr>
<td><strong>Delay Time Function</strong> (^{4})</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>CCT pin internal resistance</td>
<td>( R_{\text{CCT}} )</td>
<td>( V_1 = 4.5 ) V, ( V_2 = V_3 = 3.5 ) V</td>
<td>6.15</td>
<td>8.31</td>
<td>10.2</td>
<td>MΩ</td>
<td>3</td>
</tr>
<tr>
<td>CDT pin internal resistance</td>
<td>( R_{\text{CDT}} )</td>
<td>( V_1 = 1.5 ) V, ( V_2 = V_3 = 3.5 ) V</td>
<td>615</td>
<td>831</td>
<td>1020</td>
<td>kΩ</td>
<td>3</td>
</tr>
<tr>
<td>CIT pin internal resistance</td>
<td>( R_{\text{CIT}} )</td>
<td>–</td>
<td>123</td>
<td>166</td>
<td>204</td>
<td>kΩ</td>
<td>3</td>
</tr>
<tr>
<td>CCT pin detection voltage</td>
<td>( V_{\text{CCT}} )</td>
<td>( V_1 = 4.5 ) V, ( V_2 = V_3 = 3.5 ) V</td>
<td>( V_{\text{DS}} \times 0.68 )</td>
<td>( V_{\text{DS}} \times 0.70 )</td>
<td>( V_{\text{DS}} \times 0.72 )</td>
<td>V</td>
<td>3</td>
</tr>
<tr>
<td>CDT pin detection voltage</td>
<td>( V_{\text{CDT}} )</td>
<td>( V_1 = 1.5 ) V, ( V_2 = V_3 = 3.5 ) V</td>
<td>( V_{\text{DS}} \times 0.68 )</td>
<td>( V_{\text{DS}} \times 0.70 )</td>
<td>( V_{\text{DS}} \times 0.72 )</td>
<td>V</td>
<td>3</td>
</tr>
<tr>
<td>CIT pin detection voltage</td>
<td>( V_{\text{CIT}} )</td>
<td>( V_6 = V_{\text{DIOV}} + 0.015 ) V</td>
<td>( V_{\text{DS}} \times 0.68 )</td>
<td>( V_{\text{DS}} \times 0.70 )</td>
<td>( V_{\text{DS}} \times 0.72 )</td>
<td>V</td>
<td>3</td>
</tr>
<tr>
<td>Load short-circuiting detection delay time</td>
<td>( t_{\text{SHORT}} )</td>
<td>–</td>
<td>100</td>
<td>300</td>
<td>600</td>
<td>µs</td>
<td>2</td>
</tr>
<tr>
<td>CTLC pin response time</td>
<td>( t_{\text{CTLC}} )</td>
<td>–</td>
<td>–</td>
<td>–</td>
<td>2.5</td>
<td>ms</td>
<td>2</td>
</tr>
<tr>
<td>CTLD pin response time</td>
<td>( t_{\text{CTLD}} )</td>
<td>–</td>
<td>–</td>
<td>–</td>
<td>2.5</td>
<td>ms</td>
<td>2</td>
</tr>
<tr>
<td><strong>0 V Battery Charge Function</strong></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>0 V battery charge starting charger voltage</td>
<td>( V_{\text{CHA}} )</td>
<td>0 V battery charge function <em>available</em> ( V_1 = V_2 = V_3 = 0 ) V</td>
<td>–</td>
<td>0.8</td>
<td>1.5</td>
<td>V</td>
<td>4</td>
</tr>
<tr>
<td>0 V battery charge inhibition battery voltage</td>
<td>( V_{\text{INH}} )</td>
<td>0 V battery charge function <em>unavailable</em></td>
<td>0.4</td>
<td>0.7</td>
<td>1.1</td>
<td>V</td>
<td>2</td>
</tr>
<tr>
<td><strong>Internal Resistance</strong></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>CTLC pin internal resistance</td>
<td>( R_{\text{CTLC}} )</td>
<td>–</td>
<td>7</td>
<td>10</td>
<td>13</td>
<td>MΩ</td>
<td>5</td>
</tr>
<tr>
<td>CTLD pin internal resistance</td>
<td>( R_{\text{CTLD}} )</td>
<td>–</td>
<td>7</td>
<td>10</td>
<td>13</td>
<td>MΩ</td>
<td>5</td>
</tr>
<tr>
<td>Resistance between VM pin and VDD pin (^{5})</td>
<td>( R_{\text{VMDD}} )</td>
<td>( V_1 = V_2 = V_3 = 1.8 ) V</td>
<td>450</td>
<td>900</td>
<td>1800</td>
<td>kΩ</td>
<td>5</td>
</tr>
<tr>
<td>Resistance between VM pin and VSS pin</td>
<td>( R_{\text{VMS}} )</td>
<td>–</td>
<td>250</td>
<td>500</td>
<td>750</td>
<td>kΩ</td>
<td>5</td>
</tr>
</tbody>
</table>
### Table 5 (2/2)

<table>
<thead>
<tr>
<th>Item</th>
<th>Symbol</th>
<th>Condition</th>
<th>Min.</th>
<th>Typ.</th>
<th>Max.</th>
<th>Unit</th>
<th>Test Circuit</th>
</tr>
</thead>
<tbody>
<tr>
<td><strong>Input Voltage</strong></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Operation voltage between VDD pin and VSS pin (^6)</td>
<td>(V_{DSOP})</td>
<td>Fixed output voltage of DO pin and CO pin</td>
<td>2</td>
<td>–</td>
<td>24</td>
<td>(V)</td>
<td>–</td>
</tr>
<tr>
<td>CTLC pin change voltage (^6)</td>
<td>(V_{CTLC})</td>
<td>–</td>
<td>2.1</td>
<td>3.0</td>
<td>4.0</td>
<td>(V)</td>
<td>2</td>
</tr>
<tr>
<td>CTLD pin change voltage (^6)</td>
<td>(V_{CTLD})</td>
<td>–</td>
<td>2.1</td>
<td>3.0</td>
<td>4.0</td>
<td>(V)</td>
<td>2</td>
</tr>
<tr>
<td><strong>Input Current</strong></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Current consumption during operation</td>
<td>(I_{DPE})</td>
<td>–</td>
<td>–</td>
<td>20</td>
<td>40</td>
<td>(\mu A)</td>
<td>1</td>
</tr>
<tr>
<td>Current consumption during power-down (^5)</td>
<td>(I_{PDN})</td>
<td>(V1 = V2 = V3 = 1.5 : V)</td>
<td>–</td>
<td>–</td>
<td>0.1</td>
<td>(\mu A)</td>
<td>1</td>
</tr>
<tr>
<td>VC1 pin current</td>
<td>(I_{VC1})</td>
<td>–</td>
<td>0</td>
<td>0.8</td>
<td>2.0</td>
<td>(\mu A)</td>
<td>5</td>
</tr>
<tr>
<td>VC2 pin current</td>
<td>(I_{VC2})</td>
<td>–</td>
<td>–0.3</td>
<td>0</td>
<td>0.3</td>
<td>(\mu A)</td>
<td>5</td>
</tr>
<tr>
<td>VC3 pin current</td>
<td>(I_{VC3})</td>
<td>–</td>
<td>–0.3</td>
<td>0</td>
<td>0.3</td>
<td>(\mu A)</td>
<td>5</td>
</tr>
<tr>
<td>VC4 pin current</td>
<td>(I_{VC4})</td>
<td>–</td>
<td>–2.0</td>
<td>–0.8</td>
<td>0</td>
<td>(\mu A)</td>
<td>5</td>
</tr>
<tr>
<td><strong>Output Current</strong></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>CO pin source current</td>
<td>(I_{COH})</td>
<td>(V13 = 0.5 : V)</td>
<td>10</td>
<td>–</td>
<td>–</td>
<td>(\mu A)</td>
<td>5</td>
</tr>
<tr>
<td>CO pin leakage current</td>
<td>(I_{COL})</td>
<td>(V1 = V2 = V3 = 8 : V)</td>
<td>–</td>
<td>–</td>
<td>0.1</td>
<td>(\mu A)</td>
<td>5</td>
</tr>
<tr>
<td>DO pin source current</td>
<td>(I_{DOH})</td>
<td>(V14 = 0.5 : V)</td>
<td>10</td>
<td>–</td>
<td>–</td>
<td>(\mu A)</td>
<td>5</td>
</tr>
<tr>
<td>DO pin sink current</td>
<td>(I_{DOL})</td>
<td>(V15 = 0.5 : V)</td>
<td>–</td>
<td>–</td>
<td>–10</td>
<td>(\mu A)</td>
<td>5</td>
</tr>
</tbody>
</table>

\(^1\). Voltage temperature coefficient 1: Overcharge detection voltage  
\(^2\). Voltage temperature coefficient 2: Discharge overcurrent detection voltage  
\(^3\). Since products are not screened at high and low temperature, the specification for this temperature range is guaranteed by design, not tested in production.  
\(^4\). Refer to "Operation" for details of delay time function.  
\(^5\). For products with power-down function  
\(^6\). The S-8203A Series does not operate detection if the operation voltage between VDD pin and VSS pin (\(V_{DSOP}\)) is CTLC pin change voltage (\(V_{CTLC}\)) or CTLD pin change voltage (\(V_{CTLD}\)) or lower.
## Test Circuits

1. **Current consumption during operation, current consumption during power-down (Test circuit 1)**
   
   Set S1 and S2 to OFF.
   
   1. **Current consumption during operation (I_{OP})**
      
      Set V1 = V2 = V3 = 3.5 V, S2 to ON. \(I_{SS}\) is the current consumption during operation (I_{OP}) at that time.
   
   2. **Current consumption during power-down (I_{PD}) (With power-down function)**
      
      Set V1 = V2 = V3 = 1.5 V, S1 to ON. \(I_{SS}\) is the current consumption during power-down (I_{PD}) at that time.

2. **Overcharge detection voltage, overcharge release voltage, overdischarge detection voltage, overdischarge release voltage, discharge overcurrent detection voltage, load short-circuiting detection voltage, CTLC pin change voltage, CTLD pin change voltage, load short-circuiting detection delay time, CTLC pin response time, CTLD pin response time (Test circuit 2)**
   
   Set S3 to OFF.
   
   Confirm both VCO and VDO are in "H" (the voltage level is VDS \times 0.9 V or higher) after setting V1 = V2 = V3 = 3.5 V, V6 = V7 = V8 = 0 V (this status is referred to as initial status 1).

   2. **Overcharge detection voltage (V_{CU}), Overcharge release voltage (V_{CL})**
      
      The overcharge detection voltage (V_{CU}) is V1 when the VCO is set to "L" (the voltage level is VDS \times 0.1 V or lower) after increasing V1 gradually after setting V1 = V2 = V3 = V_{CU} - 0.05 V from the initial status 1. After that, decreasing V1 gradually, V1 is the overcharge release voltage (V_{CL}) when the VCO is set to "H" after setting V2 = V3 = 3.5 V.

   2. **Overdischarge detection voltage (V_{DL}), overdischarge release voltage (V_{DU})**
      
      The overdischarge detection voltage (V_{DL}) is V1 when the VDO is set to "L" after decreasing V1 gradually from the initial status 1. After that, increasing V1 gradually, V1 is the overdischarge release voltage (V_{DU}) when VDO is set to "H".

   By changing Vn (n = 2 to 3), users can define the overcharge detection voltage (V_{CUn}), the overcharge release voltage (V_{CLn}), the overdischarge detection voltage (V_{DLn}), the overdischarge release voltage (V_{DUn}) as well when n = 1.

   2. **Discharge overcurrent detection voltage (V_{DIOV})**
      
      The discharge overcurrent detection voltage (V_{DIOV}) is V6 when VDO is set to "L" after increasing V6 gradually from the initial status 1.

   2. **Load short-circuiting detection voltage (V_{SHORT})**
      
      The load short-circuiting detection voltage (V_{SHORT}) is V6 when VDO is set to "L" after increasing V6 gradually after setting S3 to ON from the initial status 1.

   2. **Charge overcurrent detection voltage (V_{CIOV})**
      
      The charge overcurrent detection voltage (V_{CIOV}) is V6 when VCO is set to "L" after decreasing V6 gradually from the initial status 1.

   2. **CTLC pin change voltage (V_{CTLC})**
      
      The CTLC pin change voltage (V_{CTLC}) is V7 when VCO is set to "L" after increasing V7 gradually from the initial status 1.

   2. **CTLD pin change voltage (V_{CTLD})**
      
      The CTLD pin change voltage (V_{CTLD}) is V8 when VDO is set to "L" after increasing V8 gradually from the initial status 1.

   2. **Load short-circuiting detection delay time (t_{SHORT})**
      
      Load short-circuiting detection delay time (t_{SHORT}) is a period in which VDO changes to "L" after changing V6 to 1.5 V instantaneously, after setting S3 to ON from the initial status 1.
2. 9  CTLC pin response time ($t_{CTLC}$)

CTLC pin response time ($t_{CTLC}$) is a period in which $V_{CO}$ changes to "L" after changing $V7 = V_{DS}$ instantaneously from the initial status 1.

2. 10  CTLD pin response time ($t_{CTLD}$)

CTLD pin response time ($t_{CTLD}$) is a period in which $V_{DO}$ changes to "L" after changing $V8 = V_{DS}$ instantaneously from the initial status 1.

3.  CCT pin internal resistance, CDT pin internal resistance, CIT pin internal resistance, CCT pin detection voltage, CDT pin detection voltage, CIT pin detection voltage (Test circuit 3)

Confirm both $V_{CO}$ and $V_{DO}$ are in "H" after setting $V1 = V2 = V3 = 3.5 \text{ V}$, $V6 = V9 = V10 = V11 = 0 \text{ V}$ (this status is referred to as initial status 2).

3. 1  CCT pin internal resistance ($R_{CCT}$)

The CCT pin internal resistance ($R_{CCT}$) can be defined by $R_{CCT} = V_{DS} / I_{CCT}$ by using $I_{CCT}$ when setting $V1 = 4.5 \text{ V}$ from the initial status 2.

3. 2  CDT pin internal resistance ($R_{CDT}$)

The CDT pin internal resistance ($R_{CDT}$) can be defined by $R_{CDT} = V_{DS} / I_{CDT}$ by using $I_{CDT}$ when setting $V1 = 1.5 \text{ V}$ from the initial status 2.

3. 3  CIT pin internal resistance ($R_{CIT}$)

The CIT pin internal resistance ($R_{CIT}$) can be defined by $R_{CIT} = V_{DS} / I_{CIT}$ by using $I_{CIT}$ when setting $V6 = V_{DIOV} + 0.015 \text{ V}$ from the initial status 2.

3. 4  CCT pin detection voltage ($V_{CCT}$)

The CCT pin detection voltage ($V_{CCT}$) is $V9$ when $V_{CO}$ is set to "L" after increasing $V9$ gradually, after setting $V1 = 4.5 \text{ V}$ from the initial status 2.

3. 5  CDT pin detection voltage ($V_{CDT}$)

The CDT pin detection voltage ($V_{CDT}$) is $V10$ when $V_{DO}$ is set to "L" after increasing $V10$ gradually, after setting $V1 = 1.5 \text{ V}$ from the initial status 2.

3. 6  CIT pin detection voltage ($V_{CIT}$)

The CIT pin detection voltage ($V_{CIT}$) is $V11$ when $V_{DO}$ is set to "L" after increasing $V11$ gradually, after setting $V6 = V_{DIOV} + 0.015 \text{ V}$ from the initial status 2.
4. **0 V battery charge starting charger voltage (0 V battery charge function "available")** (Test circuit 4), **0 V battery charge inhibition battery voltage (0 V battery charge function "unavailable")** (Test circuit 2)

4.1 **0 V battery charge starting charger voltage (V_{SCHA})** (0 V battery charge function "available")

The 0 V battery charge starting charger voltage (V_{SCHA}) is V12 when \( V_{CO} \) is 0.1 V or higher after increasing V12 gradually after setting V1 = V2 = V3 = 0 V, V12 = 0 V.

4.2 **0 V Battery charge inhibition battery voltage (V_{INH})** (0 V battery charge function "unavailable")

The 0 V battery charge inhibition battery voltage (V_{INH}) is V1 when \( V_{CO} \) is set to "L" after decreasing V1 gradually from the initial status 1.

5. **CTLC pin internal resistance, CTLD pin internal resistance, resistance between VM pin and VDD pin, resistance between VM pin and VSS pin, VC1 pin current, VC2 pin current, VC3 pin current, VC4 pin current, CO pin source current, CO pin leakage current, DO pin source current, DO pin sink current** (Test circuit 5)

5.1 **CTLC pin internal resistance (R_{CTLC})**

In the initial status 3, the CTLC pin internal resistance (R_{CTLC}) can be defined by \( R_{CTLC} = \frac{V_{DS}}{I_{CTLC}} \) by using I_{CTLC}.

5.2 **CTLD pin internal resistance (R_{CTLD})**

In the initial status 3, the CTLD pin internal resistance (R_{CTLD}) can be defined by \( R_{CTLD} = \frac{V_{DS}}{I_{CTLD}} \) by using I_{CTLD}.

5.3 **Resistance between VM pin and VDD pin (R_{VMD})** (With power-down function)

The resistance between VM pin and VDD pin (R_{VMD}) can be defined by \( R_{VMD} = \frac{V_{DS}}{I_{VM}} \) by using I_{VM} when setting V1 = V2 = V3 = 1.8 V from the initial status 3.

5.4 **Resistance between VM pin and VSS pin (R_{VMS})**

The resistance between VM pin and VSS pin (R_{VMS}) can be defined by \( R_{VMS} = \frac{V_{DS}}{I_{VM}} \) by using I_{VM} when setting V6 = 1.5 V, S2 to OFF, S1 to ON from the initial status 3.

5.5 **VC1 pin current (I_{VC1}), VC2 pin current (I_{VC2}), VC3 pin current (I_{VC3}), VC4 pin current (I_{VC4})**

In the initial status 3, I_{1} is the VC1 pin current (I_{VC1}), I_{2} is the VC2 pin current (I_{VC2}), I_{3} is the VC3 pin current (I_{VC3}), I_{4} is the VC4 pin current (I_{VC4}).

5.6 **CO pin source current (I_{COH}), CO pin leakage current (I_{COL})**

The CO pin source current (I_{COH}) is I_{CO} when setting V13 = 0.5 V from the initial status 3. After that, the CO pin leakage current (I_{COL}) is I_{CO} when setting V1 = V2 = V3 = 8 V, S4 to OFF, S5 to ON.

5.7 **DO pin source current (I_{DON}), DO pin sink current (I_{DOL})**

The DO pin source current (I_{DON}) is I_{DO} when setting V14 = 0.5 V, S6 to ON from the initial status 3. After that, the DO pin sink current (I_{DOL}) is I_{DO} when setting V1 = V2 = V3 = 1.8 V, V15 = 0.5 V, S6 to OFF, S7 to ON.
Figure 4  Test Circuit 1

Figure 5  Test Circuit 2

Figure 6  Test Circuit 3

Figure 7  Test Circuit 4

Figure 8  Test Circuit 5
Operation

Remark Refer to "Connection Example of Battery Protection IC".

1. Normal status
In the S-8203A Series, when the voltage of each of the batteries is in the range from overdischarge detection voltage ($V_{DLn}$) to overcharge detection voltage ($V_{CUn}$), and the VINi pin voltage is in the range from charge overcurrent detection voltage ($V_{CIOV}$) to discharge overcurrent detection voltage ($V_{DIOV}$), both of CO pin and DO pin get the $V_{DD}$ level. This is the normal status. At this time, the charge and discharge FETs are on.

2. Overcharge status
In the S-8203A Series, when the voltage of one of the batteries increases to the level of higher than $V_{CUn}$, the CO pin is set in high impedance. This is the overcharge status. The CO pin is pulled down to $EB$ by an external resistor so that the charge FET is turned off and it stops charging.

The overcharge status is released if either condition mentioned below is satisfied:
- In case that the CO pin voltage is $1/50 \times V_{DS}$ or lower, and the voltage of each of the batteries which are $V_{CUn}$ or higher is in the level of overcharge release voltage ($V_{CLR}$) or lower.
- In case that the CO pin voltage is $1/50 \times V_{DS}$ or higher, and the voltage of each of the batteries is in the level of $V_{CUn}$ or lower.

3. Overdischarge status
In The S-8203A Series, when the voltage of one of the batteries decreases to the level of $V_{DLn}$ or lower, the DO pin voltage gets the $V_{SS}$ level. This is the overdischarge status. The discharge FET is turned off and it stops discharging.

The overdischarge status is released if either condition mentioned below is satisfied:
- In case that the VM pin voltage is in the level of lower than $V_{SS}$, and the voltage of each of the batteries is in the level of $V_{DLn}$ or higher.
- In case that the VM pin voltage is $V_{DS} / 5$ (typ.) or lower and the VM pin voltage is in the level of higher than $V_{SS}$, and the voltage of each of the batteries which are $V_{DLn}$ or lower is in the level of overdischarge release voltage ($V_{CLR}$) or higher.

3.1 With power-down function
In The S-8203A Series, when it reaches the overdischarge status, the VM pin is pulled up to the $V_{DD}$ level by a resistor between VM pin and VDD pin ($R_{VM}$). If the VM pin voltage and the CO pin voltage increase to the level of $V_{DS} / 5$ (typ.) or higher, respectively, the power-down function starts to operate and almost every circuit in the S-8203A Series stops working.

The power-down function is released if either condition mentioned below is satisfied:
- The VM pin voltage gets $V_{DS} / 5$ (typ.) or lower.
- The CO pin voltage gets $V_{DS} / 5$ (typ.) or lower.

4. Discharge overcurrent status
The discharging current increases to a certain value or higher. As a result, if the status in which the VINi pin voltage increases to the level of $V_{DIOV}$ or higher, the DO pin gets the $V_{SS}$ level. This is the discharge overcurrent status. The discharge control FET is turned off and it stops discharging. In the status of discharge overcurrent, the CO pin is set in high impedance. The VM pin is pulled down to the $V_{SS}$ level by a resistor between VM pin and VSS pin ($R_{VMS}$).

The S-8203A Series has two levels for discharge overcurrent detection ($V_{DIOV}$, $V_{SHORT}$). The S-8203A Series' actions against load short-circuiting detection voltage ($V_{SHORT}$) are as well in $V_{DIOV}$.

The discharge overcurrent status is released if the following condition is satisfied:
- The VM pin voltage gets $V_{DS} / 10$ (typ.) or lower.
5. Charge overcurrent status

In the S-8203A Series, the charge current increases to a certain value or higher. As a result, if the status in which the VINI pin voltage decreases to the level of \( V_{CIOV} \) or lower, the CO pin is set in high impedance. This is the charge overcurrent status. The charge control FET is turned off and it stops charging. In this charge overcurrent status, DO pin gets the VSS level. The VM pin is pulled up to the VDD level by resistance between VM pin and VDD pin (\( R_{VM2} \)).

The charge overcurrent status is released if the following condition is satisfied.

1. The CO pin voltage gets \( \frac{1}{50} \times V_{DS} \) (typ.) or higher.

6. 0 V Battery charge function

In the S-8203A Series, regarding how to charge a discharged battery (0 V battery), users are able to select either function mentioned below.

1. Enable to charge a 0 V battery
   A 0 V battery is charged when charger voltage is higher than 0 V battery charge starting charger voltage (\( V_{CHA} \)).

2. Inhibit charging a 0 V battery
   A 0 V battery is not charged when the voltage of one of the batteries is 0 V battery charge inhibition battery voltage (\( V_{INH} \)) or lower.

Caution When the VDD pin voltage is lower than the minimum value of operation voltage between VDD pin and VSS pin (\( V_{DSOP} \)), the S-8203A Series’ action is not assured.

7. Delay time setting

In the S-8203A Series, users are able to set delay time for the period; from detecting the voltage of one of the batteries or detecting changes in the voltage at the VINI pin, to the output to the CO pin, DO pin. Each delay time is determined by a resistor in the IC and an external capacitor.

In the overcharge detection, when the voltage of one of the batteries gets \( V_{CUn} \) or higher, the S-8203A Series starts charging to the CCT pin’s capacitor (\( C_{CCT} \)) via the CCT pin’s internal resistor (\( R_{CCT} \)). After a certain period, the CO pin is set in high impedance if the voltage at the CCT pin reaches the CCT pin detection voltage (\( V_{CCT} \)). This period is overcharge detection delay time (\( t_{CU} \)).

\[
t_{CU} \text{[s]} = -\ln \left( \frac{1}{1 - \frac{V_{CCT}}{V_{DS}}} \right) \times \frac{C_{CCT} \left[ \mu F \right]}{R_{CCT} \left[ \Omega \right]}
\]

\[
= -\ln \left( 1 - 0.7 \text{ (typ.)} \right) \times \frac{8.31 \text{ [M} \Omega \text{]} \text{ (typ.)}}{10.0 \text{ [M} \Omega \text{]} \text{ (typ.)}}
\]

Overdischarge detection delay time (\( t_{DL} \)), discharge overcurrent detection delay time (\( t_{DIOV} \)), charge overcurrent detection delay time (\( t_{CIOV} \)) are calculated using the following equations as well.

\[
t_{DL} \text{[ms]} = -\ln \left( 1 - \frac{V_{CDT}}{V_{DS}} \right) \times \frac{C_{CDT} \left[ \mu F \right]}{R_{CDT} \left[ k\Omega \right]}
\]

\[
t_{DIOV} \text{[ms]} = -\ln \left( 1 - \frac{V_{CIT}}{V_{DS}} \right) \times \frac{C_{CIT} \left[ \mu F \right]}{R_{CIT} \left[ k\Omega \right]}
\]

\[
t_{CIOV} \text{[ms]} = -\ln \left( 1 - \frac{V_{CIT}}{V_{DS}} \right) \times \frac{C_{CIT} \left[ \mu F \right]}{R_{CIT} \left[ k\Omega \right]}
\]

In case \( C_{CCT} = C_{CDT} = C_{CIT} = 0.1 \left[ \mu F \right] \), each delay time \( t_{CU} \), \( t_{DL} \), \( t_{DIOV} \), \( t_{CIOV} \) is calculated as follows.

\[
t_{CU} \text{[s]} = 10.0 \left[ \text{M} \Omega \right] \text{ (typ.)} \times 0.1 \left[ \mu F \right] \times 1.0 \left[ \text{s} \right] \text{ (typ.)}
\]

\[
t_{DL} \text{[ms]} = 1000 \left[ k\Omega \right] \text{ (typ.)} \times 0.1 \left[ \mu F \right] \times 100 \left[ \text{ms} \right] \text{ (typ.)}
\]

\[
t_{DIOV} \text{[ms]} = 200 \left[ k\Omega \right] \text{ (typ.)} \times 0.1 \left[ \mu F \right] \times 20 \left[ \text{ms} \right] \text{ (typ.)}
\]

\[
t_{CIOV} \text{[ms]} = 200 \left[ k\Omega \right] \text{ (typ.)} \times 0.1 \left[ \mu F \right] \times 20 \left[ \text{ms} \right] \text{ (typ.)}
\]

Discharge overcurrent release delay time (\( t_{DIOVVR} \)) and charge overcurrent release delay time (\( t_{CIOVVR} \)) can be selected from two types, and they are calculated by \( t_{DIOV} \) and \( t_{CIOV} \) as the following equations. 1 [ms] (typ.) is the internal delay time of the S-8203A Series.

\[
(1) \ t_{DIOVVR} = t_{DIOV} \times 10 + 1 \left[ \text{ms} \right] \text{ (typ.)}, \ t_{CIOVVR} = t_{CIOV} \times 10 + 1 \left[ \text{ms} \right] \text{ (typ.)}
\]

\[
(2) \ t_{DIOVVR} = t_{DIOV} \times 0.05 + 1 \left[ \text{ms} \right] \text{ (typ.)}, \ t_{CIOVVR} = t_{CIOV} \times 0.05 + 1 \left[ \text{ms} \right] \text{ (typ.)}
\]

Load short-circuiting detection delay time (\( t_{SHORT} \)) is fixed internally.
8. CTLC pin and CTLD pin

The S-8203A Series has two pins to control. The CTLC pin controls the CO pin, the CTLD pin controls the DO pin. Thus it is possible for users to control the CO pin and DO pin independently. These controls precede the battery protection circuit.

<table>
<thead>
<tr>
<th>Table 6 Conditions Set by CTLC Pin</th>
</tr>
</thead>
<tbody>
<tr>
<td>CTLC Pin</td>
</tr>
<tr>
<td>CTLC pin voltage $\geq V_{CTLC}$</td>
</tr>
<tr>
<td>Open$^1$</td>
</tr>
<tr>
<td>CTLC pin voltage $&lt; V_{CTLC}$</td>
</tr>
</tbody>
</table>

$^1$. Pulled up by $R_{CTLC}$ when CTLC pin is open.

$^2$. The status is controlled by the voltage detection circuit.

<table>
<thead>
<tr>
<th>Table 7 Conditions Set by CTLD Pin</th>
</tr>
</thead>
<tbody>
<tr>
<td>CTLD Pin</td>
</tr>
<tr>
<td>CTLD pin voltage $\geq V_{CTLD}$</td>
</tr>
<tr>
<td>Open$^1$</td>
</tr>
<tr>
<td>CTLD pin voltage $&lt; V_{CTLD}$</td>
</tr>
</tbody>
</table>

$^1$. Pulled up by $R_{CTLD}$ when CTLD pin is open.

$^2$. The status is controlled by the voltage detection circuit.
### Timing Charts

1. Overcharge detection and overdischarge detection

- **Battery voltage**
  - \( V_{CLn} \)
  - \( V_{CLn} \)
  - \( V_{DUn} \)
  - \( V_{DLn} \)
  - \( V_{CLn} \) (n = 1 to 3)

- **DO pin voltage**
  - \( V_{SS} \)

- **CO pin voltage**
  - \( V_{DD} \)
  - \( V_{DD} \)
  - \( V_{EB} \)

- **Charger connection**
  - \( V_{SS} \)
  - \( V_{EB} \)

- **Load connection**

- **Status**
  - \( V_{EB} \) \( - \)
  - \( V_{DD} \)
  - \( V_{DD} \)
  - \( V_{DD} \)
  - \( V_{EB} \)

- **Status**
  - \( V_{EB} \) \( - \)
  - \( V_{DD} \)
  - \( V_{DD} \)
  - \( V_{DD} \)
  - \( V_{EB} \)

*1. (1): Normal status
   (2): Overcharge status
   (3): Overdischarge status
   (4): Power-down status

**Remark** The charger is assumed to charge with a constant current. \( V_{EB} \) indicates the open voltage of the charger.

*Figure 9*
2. Discharge overcurrent detection

Battery voltage

DO pin voltage

CO pin voltage

VM pin voltage

VINI pin voltage

Load connection

Status*1

*1. (1): Normal status
   (2): Discharge overcurrent status

Remark The charger is assumed to charge with a constant current. $V_{EB-}$ indicates the open voltage of the charger.

Figure 10
3. Charge overcurrent detection

Battery voltage

DO pin voltage

CO pin voltage

VM pin voltage

VINI pin voltage

Charger connection

Load connection

Status*1
(With power-down function)

Status*1
(Without power-down function)

*1. (1): Normal status
(2): Charge overcurrent status
(3): Overdischarge status
(4): Power-down status

Remark The charger is assumed to charge with a constant current. \( V_{EB} \) indicates the open voltage of the charger.

Figure 11
Connection Example of Battery Protection IC

Figure 12
Application Circuit

Figure 13 Overheat Protection via PTC

[For PTC, contact]
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TEL +81-75-955-6863
Contact Us: http://www.murata.com/contact/index.html
### Table 8 Constants for External Components

<table>
<thead>
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<th>Symbol</th>
<th>Min.</th>
<th>Typ.</th>
<th>Max.</th>
<th>Unit</th>
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<td>kΩ</td>
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<td>1</td>
<td>kΩ</td>
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*1. Set up a filter constant to be $R_{VC1} \times C_{VC1} = 68 \, \mu F \times \Omega$ or more, and to be $R_{VC1} \times C_{VC1} = R_{VC2} \times C_{VC2} = R_{VC3} \times C_{VC3} = R_{VDD} \times C_{VDD}$.

**Caution**

1. The above constants may be changed without notice.
2. It is recommended that filter constants between VDD pin and VSS pin should be set approximately to 100 $\mu F \times \Omega$.
   
   e.g., $C_{VDD} \times R_{VDD} = 1.0 \, \mu F \times 100 \, \Omega = 100 \, \mu F \times \Omega$

   Sufficient evaluation of transient power supply fluctuation and overcurrent protection function with the actual application is needed to determine the proper constants. Contact our sales office in case the constants should be set to other than 100 $\mu F \times \Omega$.
3. It has not been confirmed whether the operation is normal or not in circuits other than the example of connection. In addition, the example of connection and the constant do not guarantee proper operation. Perform thorough evaluation using the actual application to set the constant.
Precautions

- The application conditions for the input voltage, output voltage, and load current should not exceed the package power dissipation.
- Batteries can be connected in any order, however, there may be cases when discharging cannot be performed when a battery is connected. In this case, short the VM pin and VSS pin or connect the battery charger to return to the normal status.
- If both an overcharge battery and an overdischarge battery are included among the whole batteries, the condition is set in overcharge status and overdischarge status. Therefore either charging or discharging is impossible.
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
- ABLIC Inc. claims no responsibility for any disputes arising out of or in connection with any infringement by products including this IC of patents owned by a third party.
Characteristics (Typical Data)

1. Current consumption

1.1 $I_{OPE}$ vs $V_{DS}$

1.2 $I_{OPE}$ vs $T_a$

1.3 $I_{PDN}$ vs $V_{DS}$

1.4 $I_{PDN}$ vs $T_a$
2. Overcharge detection / release voltage, overdischarge detection / release voltage, discharge overcurrent detection voltage, load short-circuiting detection voltage, charge overcurrent detection voltage

2.1 $V_{CU} \text{ vs } Ta$

![Graph of $V_{CU}$ vs $Ta$]

2.2 $V_{CL} \text{ vs } Ta$

![Graph of $V_{CL}$ vs $Ta$]

2.3 $V_{DL} \text{ vs } Ta$

![Graph of $V_{DL}$ vs $Ta$]

2.4 $V_{DU} \text{ vs } Ta$

![Graph of $V_{DU}$ vs $Ta$]

2.5 $V_{DIOV} \text{ vs } Ta$

![Graph of $V_{DIOV}$ vs $Ta$]

2.6 $V_{SHORT} \text{ vs } Ta$

![Graph of $V_{SHORT}$ vs $Ta$]

2.7 $V_{CIOV} \text{ vs } Ta$

![Graph of $V_{CIOV}$ vs $Ta$]
3. CCT pin internal resistance / detection voltage, CDT pin internal resistance / detection voltage, CIT pin internal resistance / detection voltage and short-circuiting detection voltage delay time

3.1 \( R_{\text{CCT}} \) vs \( Ta \)  

3.2 \( V_{\text{CCT}} \) vs \( Ta \) (\( V_{DS} = 11.5 \) V)

3.3 \( R_{\text{CDT}} \) vs \( Ta \)  

3.4 \( V_{\text{CDT}} \) vs \( Ta \) (\( V_{DS} = 8.5 \) V)

3.5 \( R_{\text{CIT}} \) vs \( Ta \)  

3.6 \( V_{\text{CIT}} \) vs \( Ta \) (\( V_{DS} = 10.5 \) V)

3.7 \( t_{\text{SHORT}} \) vs \( Ta \)
4. CO pin source / leakage current, DO pin source / sink current

4.1 $I_{COH}$ vs $V_{CO}$

4.2 $I_{COL}$ vs $V_{CO}$

4.3 $I_{DODH}$ vs $V_{DO}$

4.4 $I_{DOLD}$ vs $V_{DO}$
No. FT016-A-P-SD-1.2

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ABLIC Inc.
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Enlarged drawing in the central part

No. FT016-A-R-S1-1.0

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2.2-2018.06